

Rotary ultrasonic machining of single-crystal silicon



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1. Calculation for the maximum pressure during RUM

Highest force $F_H = 81.57$ N (Experiment Table 5)

Lowest force $F_L = 57.56$ N (Experiment Table 5)

Tool inner diameter $d_i = 10$ mm

Tool outer diameter $d_o = 12$ mm

Area $A_0 = \frac{\pi}{4}(d_o^2 - d_i^2) = 35.558$ mm²

Abrasive concentration $C_a = 100$ [1]

Abrasive material density $\rho = 3.52 \times 10^{-3} \frac{g}{mm^3}$ [1]

Grit/Mesh size = 100–120 [1]

Abrasive size $S_a = 0.137$ mm [1]

Abrasive edge radius = 1–10 μ m [2]

Diamond elastic modulus $E = 1200$ Gpa [3]

Silicon elastic modulus : 130 Gpa [4]

Poisson's ratio for diamond = 0.0691 ~ 0.2 [5]

Poisson's ratio for silicon = 0.26 [4]

Composite $\frac{1}{E^*} = \frac{1-\nu_d^2}{E_d} + \frac{1-\nu_s^2}{E_s}$

$E^* = 124.97$ Gpa

Number of active abrasives on the edge of a RUM cutting tool

$$N = \left(\frac{(C_a \times 0.88^{-3})}{\left(100 \times \left(\frac{\pi}{6}\right) \times \rho \times S_a^3\right)} \right)^{\frac{2}{3}} \times A_0 \quad [6]$$

$N = 79.43 \sim 80$

Peak pressure $P_0 = \frac{3}{2} \left(\frac{16WE^{*2}}{9\pi^3NR^2} \right)^{\frac{1}{3}}$ Hertzian contact [7]

For highest load, $P_0 = \frac{3}{2} \left(\frac{16 \times 81.57 \times (124.97 \times 10^9)^2}{9\pi^3 \times 80 \times (10 \times 10^{-6})^2} \right)^{\frac{1}{3}} = 31.35$ GPa, $R = 10 \mu$ m



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For highest load, $P_0 = \frac{3}{2} \left(\frac{16 \times 81.57 \times (124.97 \times 10^9)^2}{9\pi^3 \times 80 \times (1 \times 10^{-6})^2} \right)^{\frac{1}{3}} = 145.52 \text{ GPa}$, $R = 1 \text{ }\mu\text{m}$

For lowest load, $P_0 = \frac{3}{2} \left(\frac{16 \times 57.56 \times (124.97 \times 10^9)^2}{9\pi^3 \times 80 \times (10 \times 10^{-6})^2} \right)^{\frac{1}{3}} = 27.91 \text{ GPa}$, $R = 10 \mu\text{m}$

For lowest load, $P_0 = \frac{3}{2} \left(\frac{16 \times 57.56 \times (124.97 \times 10^9)^2}{9\pi^3 \times 80 \times (1 \times 10^{-6})^2} \right)^{\frac{1}{3}} = 129.55 \text{ GPa}$, $R = 1 \text{ }\mu\text{m}$

Table S1. Calculated maximum pressure during RUM.

Cutting force (N)	Abrasive radius ((μm))	Peak pressure (GPa)
57.56	10	31.35
57.56	1	145.52
81.57	10	27.91
81.57	1	129.55

Therefore, with rotary ultrasonic machining (RUM) cutting tool the local peak pressure was more than the pressure induced phase transformation (Si-I $\rightarrow$ Si-II), requirement for creating ductile deformation zones [8].

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